

INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATION

(PTO-1449)

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APPLICANT

Hidenori KAMEI, et al.

FILING DATE

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GROUP



## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
Dme	5,932,896	8/3/99	Sugiura et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

Dme	"p-type Conduction in As-Grown Mg-Doped GaN Grown by Metalorganic Chemical Vapor Deposition" by Sugiura et al., Applied Physics Letters, Vol. 72, No. 14 (April 6, 1998), pp. 1748-1750.

EXAMINER D.M. Collins	DATE CONSIDERED 1-2-02
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